

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

2SC6096 — NPN Epitaxial Planar Silicon Transistor

High-Voltage Switching Applications

Applicaitons

• DC / DC converter, relay drivers, lamp drivers, motor drivers, inverter

Features

- · Adoption of FBET, MBIT process
- · Low collector-to-emitter saturation voltage
- · High allowable power dissipation

- · Large current capacity
- · High-speed switching
- · Halogen free compliance

Specifications

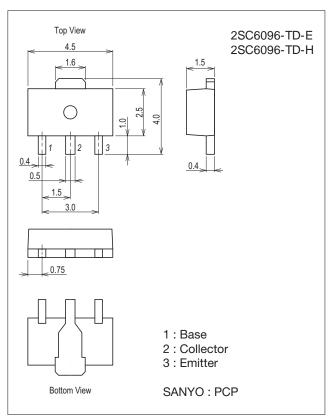
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO	Containent	120	V
Collector-to-Emitter Voltage	VCES		120	V
	VCEO		100	V
Emitter-to-Base Voltage	VEBO		6.5	V
Collector Current	IC		2	А
Collector Current (Pulse)	ICP		3	Α

Continued on next page.

Package Dimensions

unit : mm (typ) 7007B-004



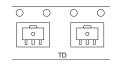
Product & Package Information

• Package : PCP

• JEITA, JEDEC : SC-62, SOT-89, TO-243

• Minimum Packing Quantity: 1,000 pcs./reel

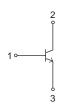
Packing Type: TD



Marking



Electrical Connection



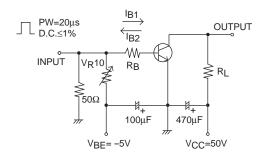
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Parameter	Symbol	Conditions	Ratings	Unit
Base Current I _B			400	mA
Collector Dissination	PC	When mounted on ceramic substrate (250mm ² ×0.8mm)	1.3	W
Collector Dissipation		Tc=25°C	3.5	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
Farameter	Symbol	Conditions	min	typ	max	Offic
Collector Cutoff Current	ICBO	V _{CB} =80V, I _E =0A			1	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =4V, I _C =0A			1	μΑ
DC Current Gain	hFE	V _{CE} =5V, I _C =100mA	300		600	
Gain-Bandwidth Product fT		VCE=10V, IC=300mA	CE=10V, IC=300mA 300			MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		13		pF
Collector-to-Emitter Saturation Voltage	VCE(sat)	I _C =1A, I _B =100mA		100	150	mV
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C =1A, I _B =100mA		0.85	1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=10μA, IE=0A	120			V
Collector-to-Emitter Breakdown Voltage	V(BR)CES	I _C =100μA, R _{BE} =0Ω	120			V
Collector-to-Efflitter Breakdown voltage	V(BR)CEO	IC=1mA, RBE=∞	100			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =10μA, I _C =0A	6.5			V
Turn-ON Time	ton			40		ns
Storage Time	t _{stg}	See specified Test Circuit.		1100		ns
Fall Time t _f				40		ns

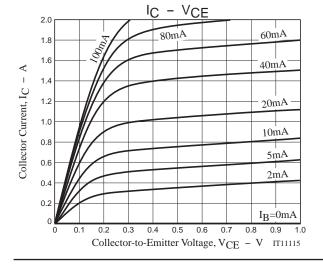
Switching Time Test Circuit

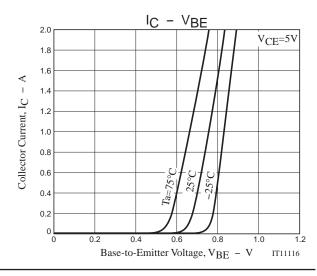


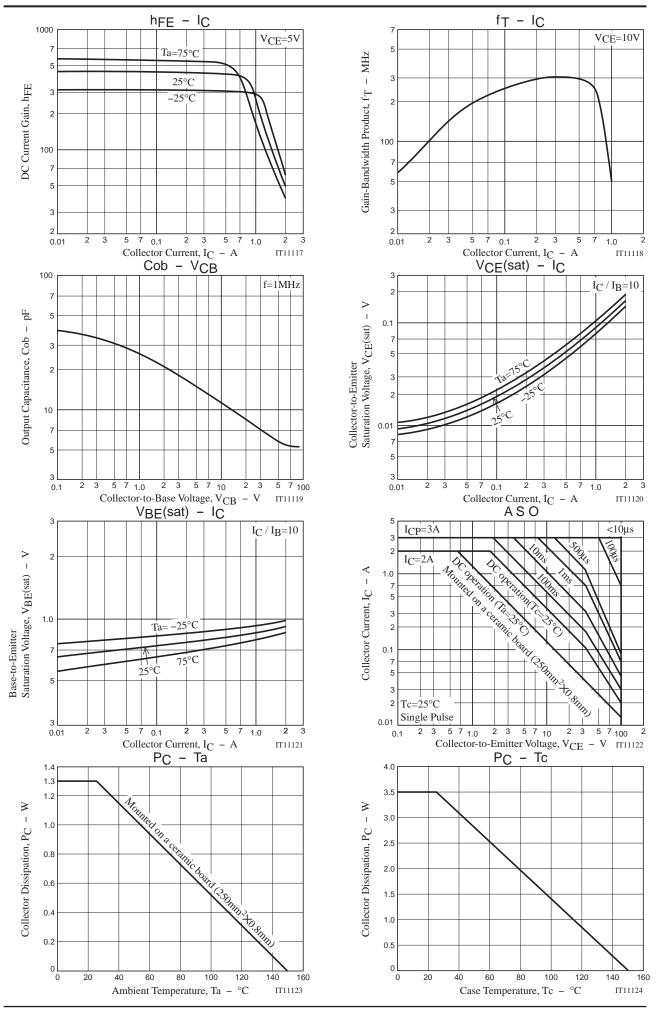
 $I_{C}=10I_{B1}=-10I_{B2}=0.5A$

Ordering Information

Device Package		Shipping	memo	
2SC6096-TD-E	PCP	1,000pcs./reel	Pb Free	
2SC6096-TD-H	PCP	1,000pcs./reel	Pb Free and Halogen Free	





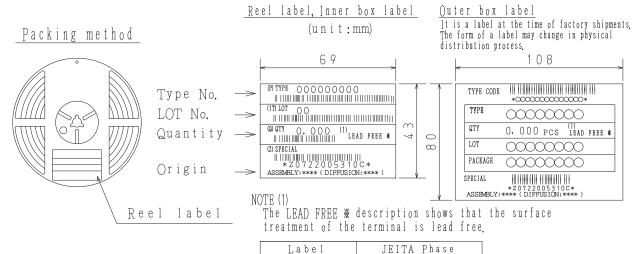


Embossed Taping Specification

2SC6096-TD-E, 2SC6096-TD-H

1. Packing Format

Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing format		
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)	
PCP	PCP	1, 000	4,000	24,000	4 reels contained	6 inner boxes contained	
					Dimensions:mm (external)	Dimensions:mm (external)	
					183×72×185	440×195×210	



LEAD FREE 3

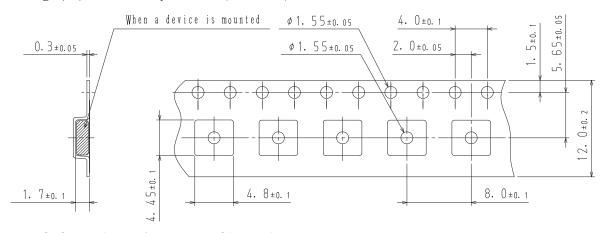
LEAD FREE 4

JEITA Phase 3A

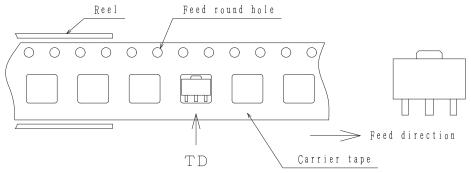
JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction



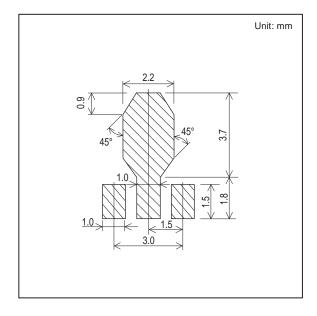
Those with pin 1 index on the feed hole side·····TD

Outline Drawing

2SC6096-TD-E, 2SC6096-TD-H

Mass (g) Unit 0.058 mm 4. 5±0. 1 1. 6±0. 2 _ 1.5±0.1_ 2. 5±0. 1 4. 0±0. 2 1. 0±0. 2 0. 4+0. 08 0. 4±0. 03 0. 5^{+0. 05} 1. 5±0. 2 3. O±0. 2 0. 75 0.10 *1:Lot indication

Land Pattern Example



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